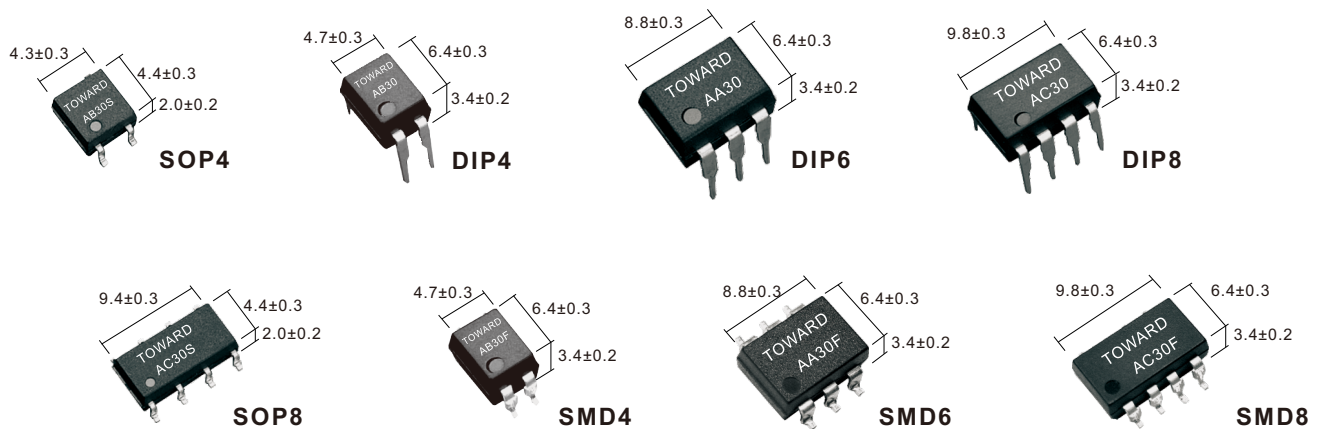


400V · 1a/2a

Features

- Contact Form 1a / 2a
- Load Voltage 400V Max.
- Operation LED Current 3.0mA Max.
- Load Current 120mA Max.
- On-Resistance 24Ω Typ.
- Output Capacitance 100pF Typ.
- Low Off-State Leakage Current 1.0 μA Max.
- Suffix -H for DIP/SMD I/O Breakdown Voltage 5000Vrms Min.
- Suffix -H for SOP I/O Breakdown Voltage 3750Vrms Min.

Outline:(Unit:mm) pitch:2.54 mm



Terminal Identification 電路結構圖

Terminal Identification		
AB30(F)(S)	AA30(F)	AC30(F)(S)
<p>1: Anode (LED) 2: Cathode (LED) 3,4: Drain (MOS FET)</p>	<p>1: Anode (LED) 2: Cathode (LED) 3: NC 4,6: Drain (MOS FET) 5: Source (MOS FET)</p>	<p>1,3: Anode (LED) 2,4: Cathode (LED) 5,6,7,8: Drain (MOS FET)</p>

PhotoDMOS-FET Relay
General Purpose

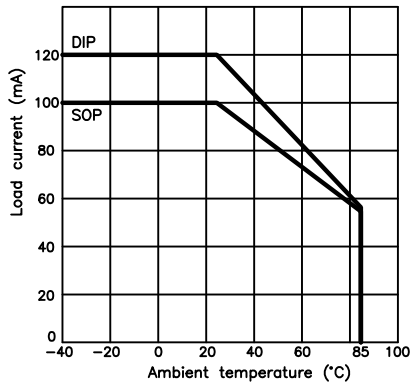
Absolute Maximum Ratings 絕對最大定格 (Ambient Temperature 周圍溫度 : 25°C)

Item		Symbol	Value				
Outline Package			SOP 4/8		DIP 4/8 SMD 4/8		DIP 6 SMD 6
			1CH	2CH	1CH	2CH	1CH
Input 輸入	Continuous LED Current 連續的LED電流	I _F	50mA				
	Peak LED Current LED的峰值電流(f=100 Hz, duty=1%)	I _{FP}	500mA				
	LED Reverse Voltage 逆向的LED電壓	V _R	5V				
	Input Power Dissipation 容許損失	P _{In}	75mW				
Output 輸出	Load Voltage 負荷電壓	V _L	400V (AC peak or DC)				
	Load Current 負荷電流 (mA)	I _L	100	85	120	100	120
	Peak Load Current 峰值負荷電流 (1 ms, 1 shot) (mA)	I _{Peak}	600	600	600	600	600
	Output Power Dissipation 電流損耗 (mW)	P _{Out}	300	450	450	600	450
Total Power Dissipation 全損耗 (mW)		P _T	350	500	500	650	500
I/O Breakdown Voltage 入/出力間絕緣電壓 (Vrms)		V _{I/O}	1500	1500	3750	3750	3750
Operating Temperature 使用時周圍溫度		T _{Opr}	-40°C ~ +85°C				
Storage Temperature 周圍保存溫度		T _{Stg}	-40°C ~ +100°C				

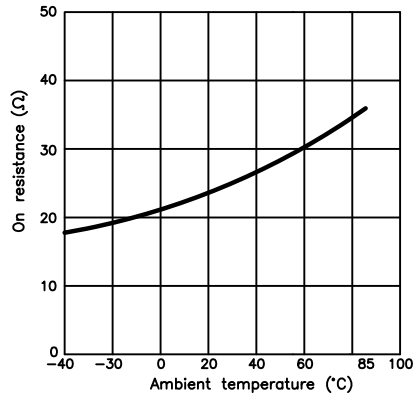
Electrical Specifications LED順向電壓(Ambient Temperature 周圍溫度 : 25°C)

Item		Symbol	MIN.	TYP.	MAX.	Units	Conditions
Input 輸入	LED Forward Voltage LED順向電壓	V _F	1.0	1.17	1.5	V	I _F =10mA
	Operation LED Current LED的動作電流	I _{F On}		0.9	3.0	mA	
	Recovery LED Voltage LED的恢復電壓	V _{F Off}	0.5	1.0		V	
Output 輸出	On-Resistance 導通電阻 Drain to Drain	R _{On}		24	30	Ω	I _F =5mA, I _L =Rating Time to flow is within 1sec.
	Off-State Leakage Current 開路狀態時的電流	I _{Leak}			1.0	μA	V _L =400V
	Output Capacitance 輸出端容量	C _{Out}		100		pF	V _L =0V, f=1MHz
Transmission 傳達	Turn-On Time 動作時間	T _{On}		0.25	0.5	ms	I _F =5mA I _L =Rating (for SOP type)
	Turn-Off Time 復位時間	T _{Off}		0.04	0.2	ms	
	Turn-On Time 動作時間	T _{On}		0.2	1.0	ms	I _F =10mA, I _L =Rating (for DIP/SMD type)
	Turn-Off Time 復位時間	T _{Off}		0.05	0.5	ms	
Coupled 結合	I/O Insulation Resistance 輸入/出間的絕緣阻抗	R _{I/O}	10 ⁹			Ω	
	I/O Capacitance 輸入/力端的靜電容量	C _{I/O}		1.3		pF	f=1MHz

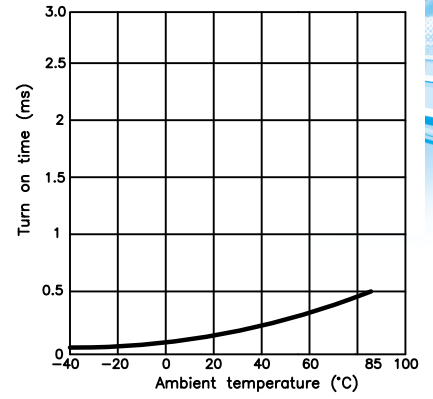
Load current Vs. Ambient temperature



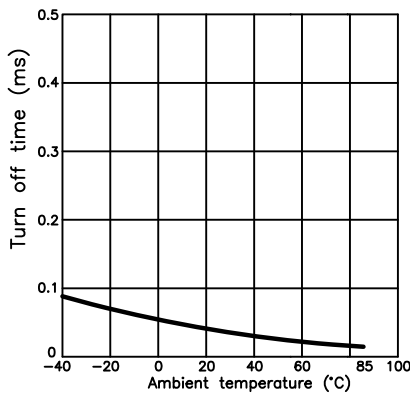
On resistance Vs. Ambient temperature



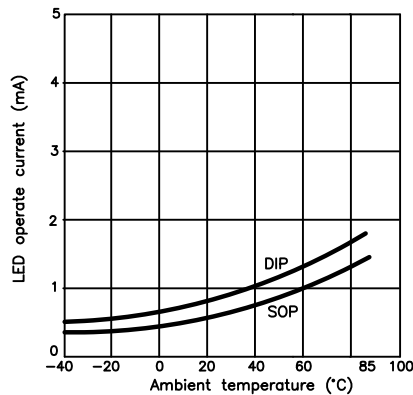
Turn on time Vs. Ambient temperature



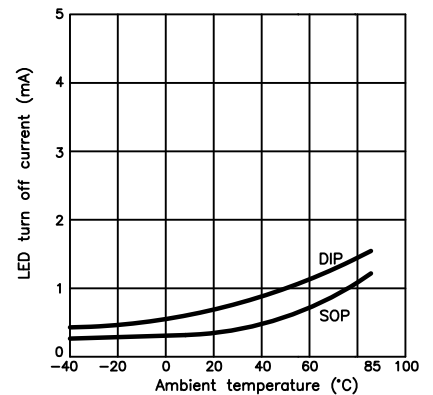
Turn off time Vs. Ambient temperature



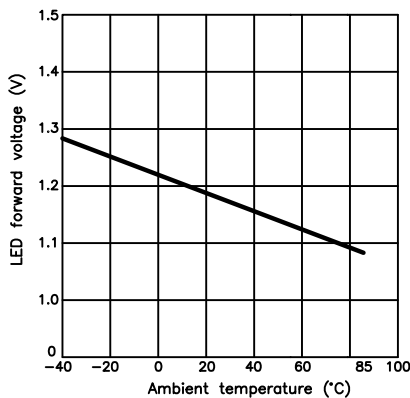
LED operate current Vs. Ambient temperature



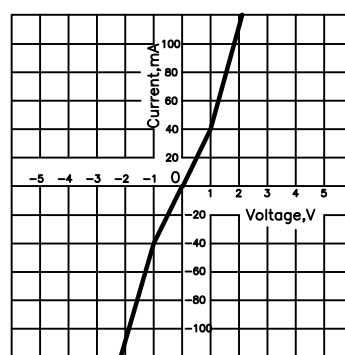
LED Turn off current Vs. Ambient temperature



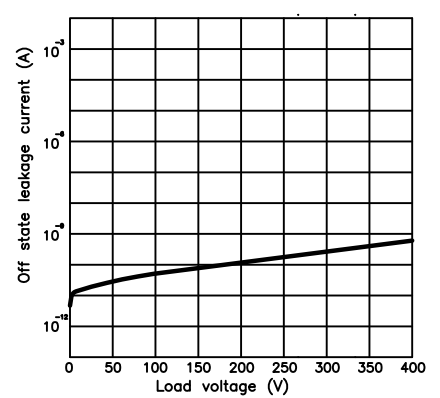
LED forward voltage Vs. Ambient temperature



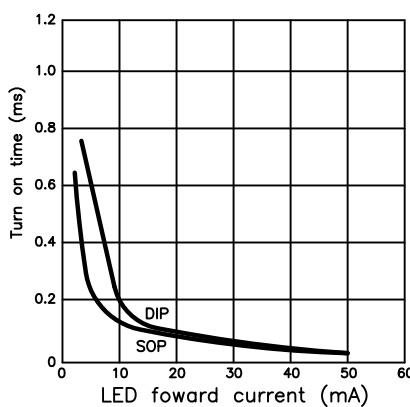
Voltage Vs. current characteristics of output at MOS portion



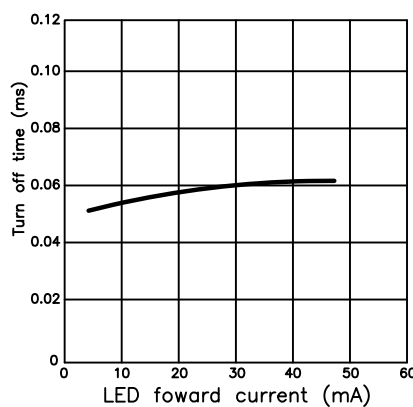
Off state leakage current



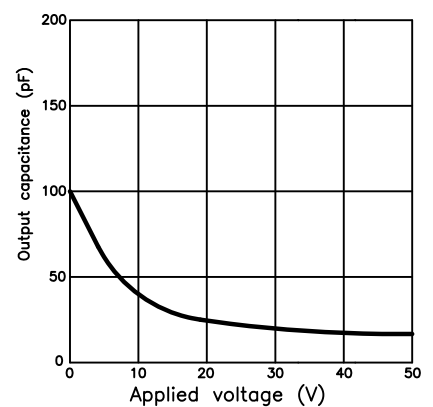
LED forward current Vs. turn on time characteristics



LED forward current Vs. turn off time characteristics



Applied voltage Vs. output capacitance characteristics



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General Purpose